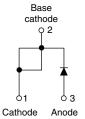


Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt®





10-22040	TO	-220	AC
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PRODUCT SUMMARY					
Package	TO-220AC				
I _{F(AV)}	30 A				
V_{R}	600 V				
V _F at I _F	2.60 V				
t _{rr} (typ.)	See Recovery table				
T _J max.	175 °C				
Diode variation	Single die				

FEATURES

- Reduced Q_{rr} and soft recovery
- 175 °C T_{.1} maximum
- For PFC CRM/CCM operation
- · Low forward voltage drop
- Low leakage current
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level





DESCRIPTION/APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V_{RRM}		600	V			
Average rectified forward current	I _{F(AV)}	T _C = 103 °C	30	٨			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	200	А			
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN. TYP. MA				
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-		
Converd veltage	V _F	I _F = 30 A	-	2.0	2.6	V	
Forward voltage		I _F = 30 A, T _J = 150 °C	-	1.34	1.75		
Deverse leekees europt	,	V _R = V _R rated	-	0.3	50		
Reverse leakage current	I _R	$T_{\rm J} = 150 ^{\circ}\text{C}, V_{\rm R} = V_{\rm R} \text{rated} \qquad \qquad - \qquad 60$		500	μΑ		
Junction capacitance	C _T	V _R = 600 V	-	33	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nΗ	

VS-30ETH06PbF

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 A, dI_F/dt =$	$50 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	-	28	35		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	31	-	ns	
		T _J = 125 °C	$I_F = 30 \text{ A}$	-	77	-		
Peak recovery current	I _{RRM}	T _J = 25 °C		-	3.5	-	А	
		IRRM	T _J = 125 °C	dI _F /dt = 200 A/μs V _R = 200 V	=	7.7	-	A
Reverse recovery charge	0	T _J = 25 °C	11	-	65	-	nC	
	Q _{rr}	T _J = 125 °C		-	345	-	IIC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	0.7	1.1		
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-		
Weight			-	2.0	-	g	
vveignt			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AC		30ETH06			



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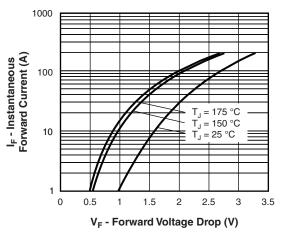


Fig. 1 - Typical Forward Voltage Drop Characteristics

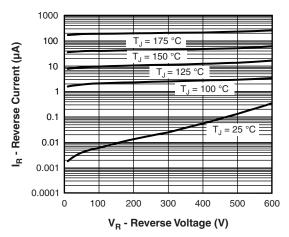


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

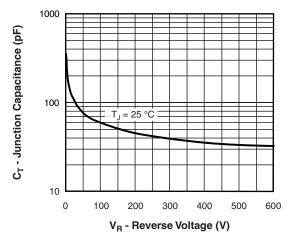


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

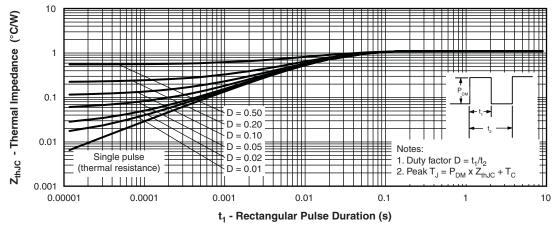


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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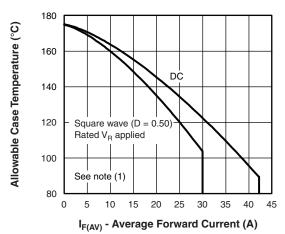


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

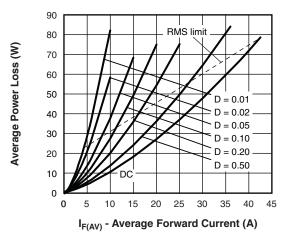


Fig. 6 - Forward Power Loss Characteristics

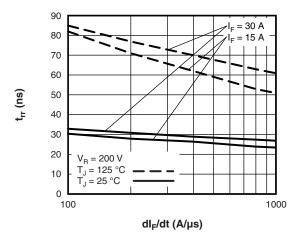


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

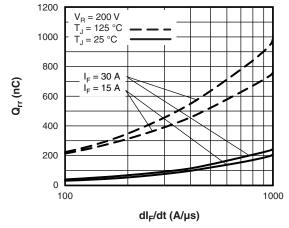


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (\text{Pd} + \text{Pd}_{\text{REV}}) \times \text{R}_{\text{th}JC}; \\ \text{Pd} = \text{Forward power loss} = I_{\text{F(AV)}} \times \text{V}_{\text{FM}} \text{ at } (I_{\text{F(AV)}}/D) \text{ (see fig. 6)}; \\ \text{Pd}_{\text{REV}} = \text{Inverse power loss} = \text{V}_{\text{R1}} \times I_{\text{R}} (1 - D); I_{\text{R}} \text{ at } \text{V}_{\text{R1}} = \text{Rated V}_{\text{R}} \\ \end{array}$



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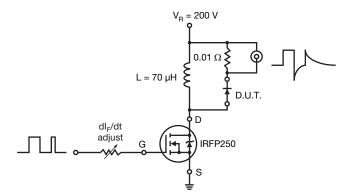
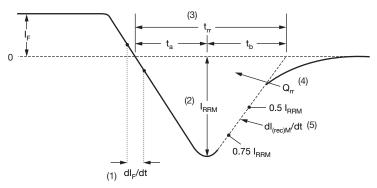


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RBM} and 0.50 I_{RBM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

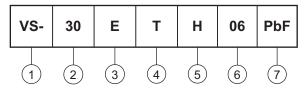
Fig. 10 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors Hyperfast Rectifier, 30 A FRED Pt®



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (30 = 30 A)

3 - E = Single diode

4 - Package:

T = TO-220

5 - H = Hyperfast recovery

6 - Voltage rating (06 = 600 V)

7 - PbF = Lead (Pb)-free

Tube standard pack quantity: 50 pieces

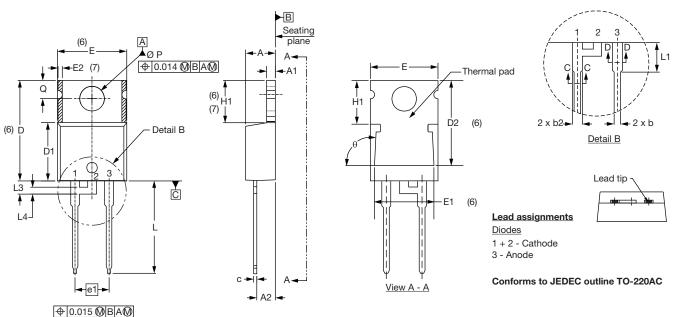
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95221				
Part marking information	www.vishay.com/doc?95224				
SPICE model	www.vishay.com/doc?95422				



Vishay Semiconductors

TO-220AC

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIM	MILLIMETERS INCHES		INCHES	
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
L3	1.78	2.13	0.070	0.084	
L4	0.76	1.27	0.030	0.050	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° to 93°		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline





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